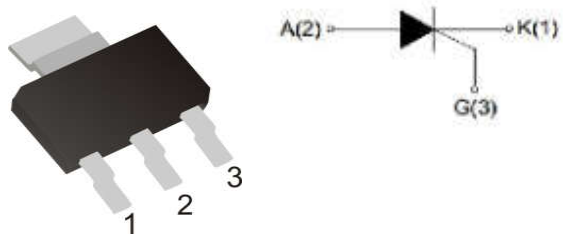
0.8A Sensitive Gate SCRs

Product Summary

Symbol	Value	Unit
$I_{T(AV)}$	0.8	A
V_{DRM} V_{RRM}	600/800	V
V_{TM}	1.5	V

Circuit diagram



SOT-223

Features

With high ability to withstand the shock loading of arge current, Provide high dv/dt rate with strong resistance to electromagnetic interference

Application

Power charger, T-tools, massager, solid staterelay, AC Motor speed regulation and so on.

Order Information

Part Number	Package	Marking	packing	packing Quantity
BT169GW	SOT-223	BT169GW XXXX	13" T&R	2500PCS/Tape

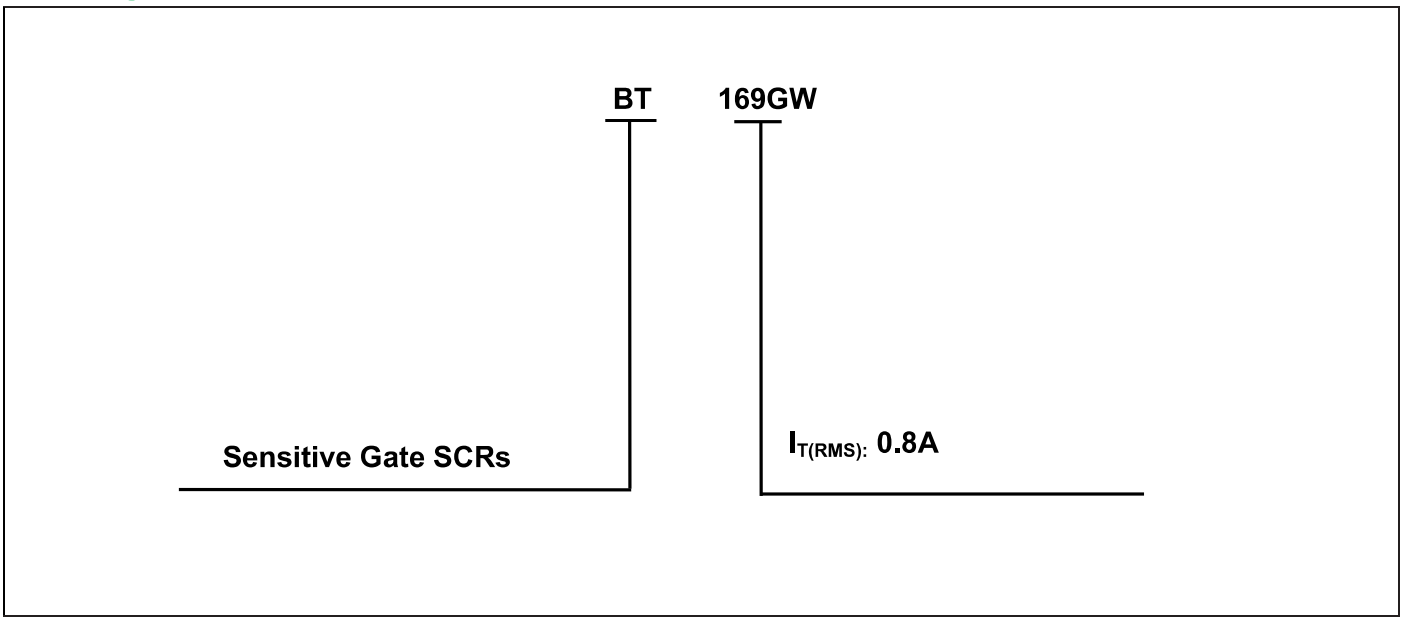
Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	V_{DRM}	600/800	V
Repetitive peak reverse voltage	V_{RRM}	600/800	V
On state average current	$I_{T(AV)}$	0.5	A
RMS on-state current	$I_{T(RMS)}$	0.8	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	10	A
I^2t value for fusing (tp=10ms)	I^2t	3.2	A^2s
Critical rate of rise of on-state current (I_G =2 x I_{GT})	dI/dt	50	A/us
Peak gate current	I_{GM}	0.2	A
Gate peak power	P_{GM}	0.5	W
Average gate power dissipation	$P_{G(AV)}$	0.1	W
Junction Temperature	T_J	-40~+110	°C
Storage Temperature	T_{STG}	-40 ~+150	°C

Electrical characteristics (T_A=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition		Value			Unit
				Min	Typ	Max	
Gate trigger current	I_{GT}	V_D=6V,R_L=100Ω, RGK=1KΩ,Fig.6		10	20	60	uA
Gate trigger voltage	V_{GT}	V_D=12V, RL=100Ω, RGK=1KΩ		-	-	0.8	V
Gate non-trigger voltage	V_{GD}	V_D =1/2V_{DRM}, RGK=1KΩ,Tj=110°C		0.2	-	-	V
latching current	I_L	IG=1.2IGT,Fig.6		-	-	4	mA
Holding current	I_H	V_D =24V,I_{TM}=4A RGK=1kΩ,Tj=25°C, Fig.6		-	1	3	mA
Critical-rate of rise of commutation voltage	dV_D/dt	V_D=2/3V_{DRM} , RGK=1KΩ,Tj=110°C		10	-	-	V/us
STATIC CHARACTERISTICS							
Forward "on" voltage	V_{TM}	I_{TM} =1.2A,Fig.4		-	-	1.5	V
Repetitive Peak Off-State Current	I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25°C	-	-	5	uA
Repetitive Peak Reverse Current	I_{RRM}		T_j=110°C	-	-	100	uA
THERMAL RESISTANCES							
Thermal resistance	Rth(j-c)	Junction to case		TYP.		20	°C/W
	Rth(j-a)	Junction to ambient	S=5cm2	TYP.		60	°C/W

Ordering Information



Typical Characteristics

FIG1 Maximum power dissipation versus RMS on-state current

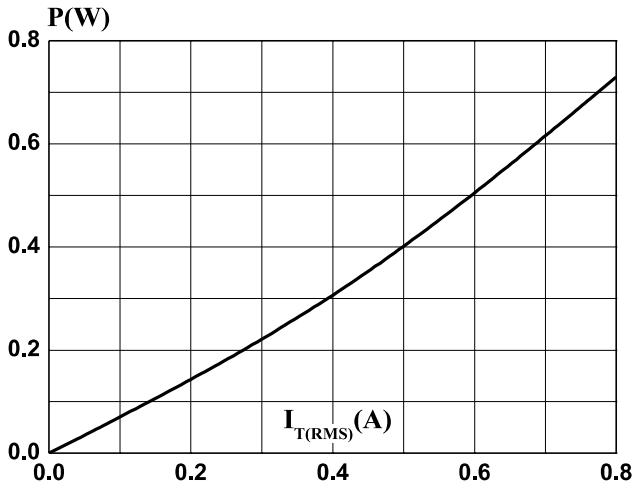


FIG2 RMS on-state current versus case temperature

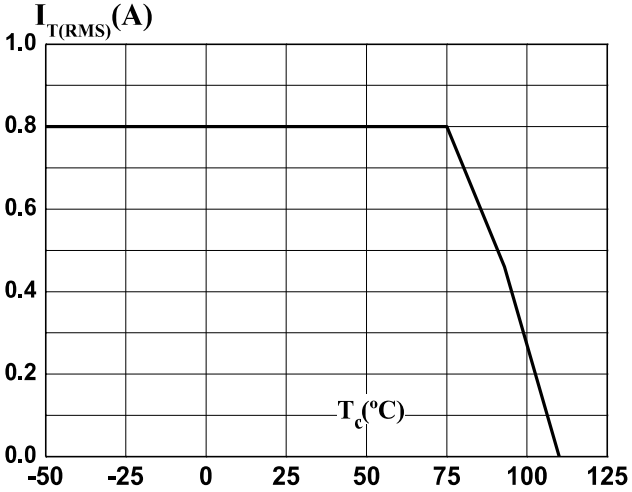


FIG3 Surge peak on-state current versus number of cycles

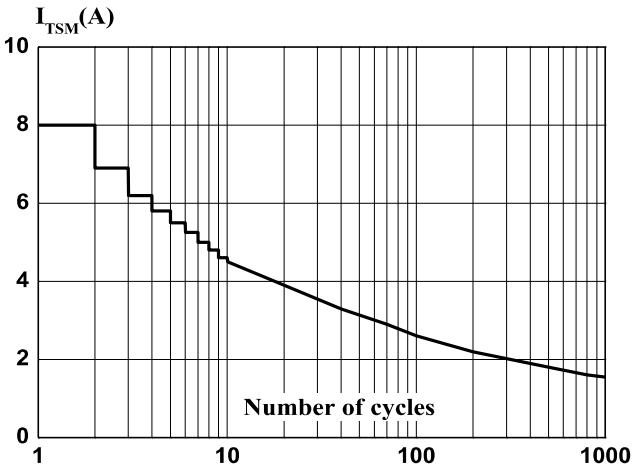


FIG4 On-state characteristics (maximum values)

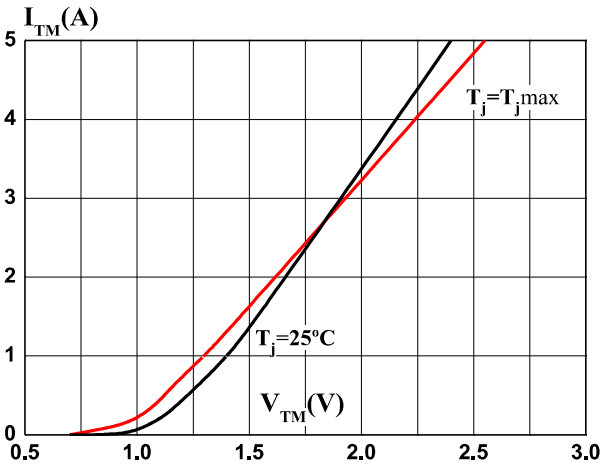


FIG5 Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t (dI/dt < 100A/μs)

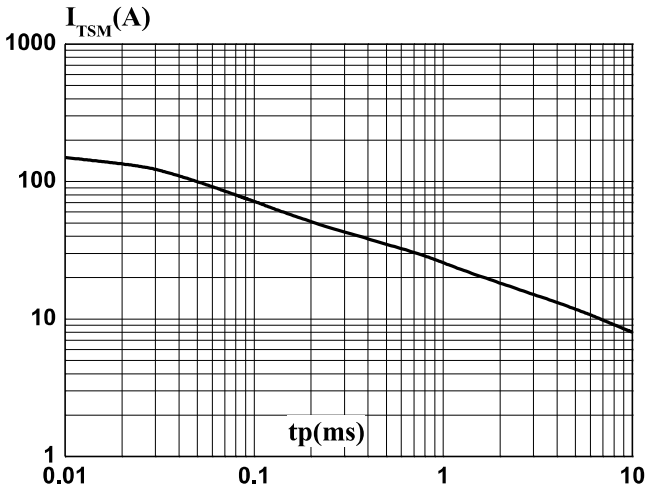
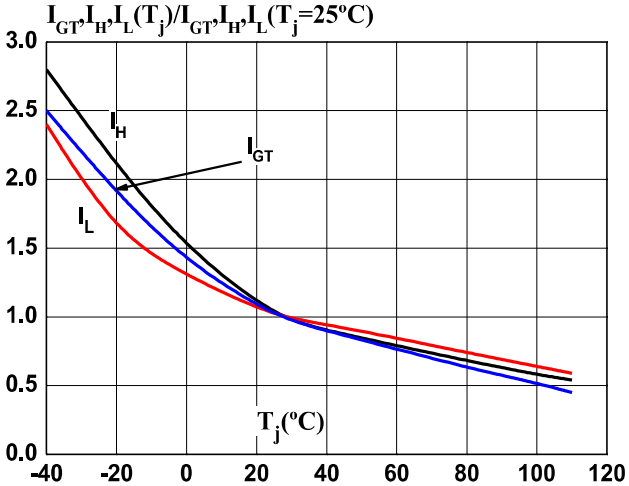
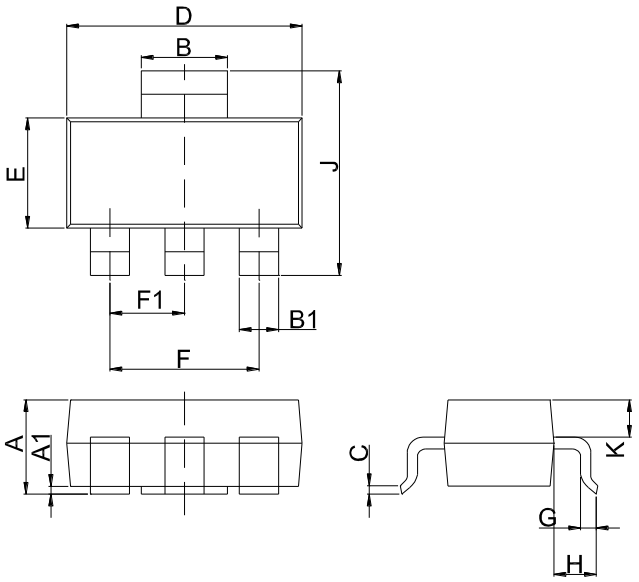


FIG6 Relative variations of gate trigger current, holding current and latching current versus junction temperature



Package Information

SOT-223



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0	0.06	0.10	0	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F		4.6			0.181	
F1		2.3			0.091	
G	0.7	0.9	1.1	0.028	0.035	0.043
H	1.5	1.75	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K	0.8	0.9	1.0	0.031	0.035	0.039